

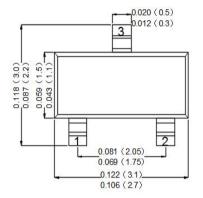


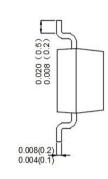
### **PNP Silicon Epitaxial Planar Transistor**

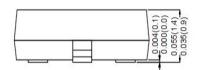
#### **Features**

• For general purpose AF amplifier

#### **SOT-23**







Dimensions in inches and (millimeters)

#### **Mechanical Data**

- Case:Molded Plastic,SOT-23
- Epoxy:UL 94V-0 rate flame retardant
- Terminals:Plated Leads Solderable perMIL-STD-750,Method-2026.
- Marking: marked on body
- Mounting Position : Any.
- Equivalent Circuit:

# Maximum Ratings Maximum Ratings (Rating at 25°C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Collector Base Voltage	-V <sub>CBO</sub>	20	V
Collector Emitter Voltage	-V <sub>CEO</sub>	15	V
Emitter Base Voltage	-V <sub>EBO</sub>	5	V
Collector Current	-I <sub>C</sub>	700	mA
Collector Current (Pulse)	-I <sub>CP</sub>	1.5	Α
Power Dissipation	P <sub>tot</sub>	200	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	Ts	- 55 to + 150	°C

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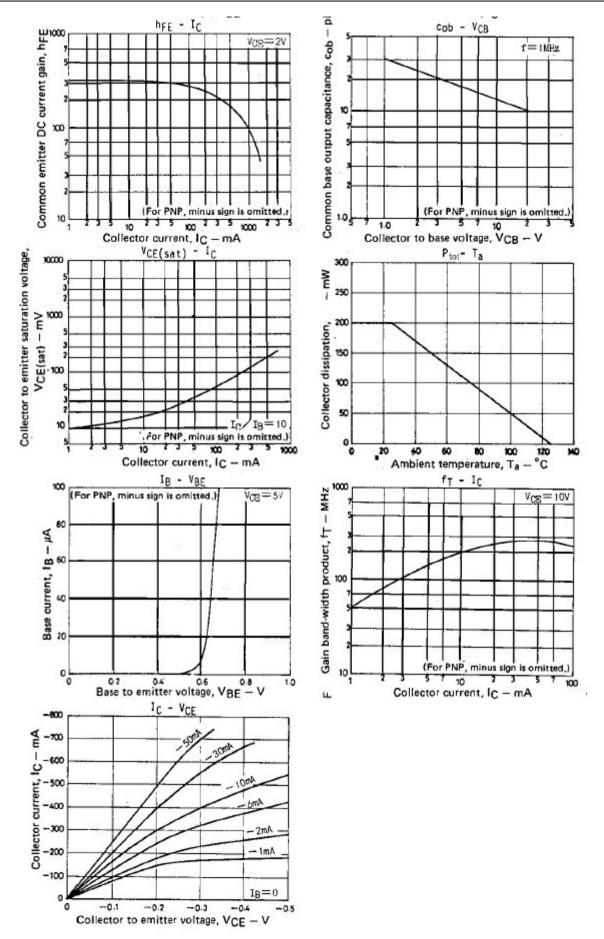
## Electrical Characteristics (Rating at 25°C ambient temperature unless otherwise specified.)

Parameter	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at $-V_{CE} = 2 \text{ V}$ , $-I_{C} = 50 \text{ mA}$	$h_FE$	200	-	400	-
at $-V_{CE} = 2 \text{ V}$ , $-I_{C} = 500 \text{ mA}$	$h_{FE}$	80	-	-	-
Collector Cutoff Current	-1	_	_	100	nA
at $-V_{CB} = 15 \text{ V}$	-I <sub>CBO</sub>		-	100	IIA
Emitter Cutoff Current	-I <sub>EBO</sub>	-	-	100	nA
at $-V_{EB} = 4 \text{ V}$					
Collector Base Breakdown Voltage	-V <sub>(BR)CBO</sub>	20	_	_	V
at - $I_C$ = 10 $\mu$ A	• (BR)CBO	20	_	_	V
Collector Emitter Breakdown Voltage	-V <sub>(BR)CEO</sub>	15	_	_	V
at - $I_C$ = 100 $\mu$ A	V (BR)CEO	10	_	_	V
Emitter Base Breakdown Voltage	-V <sub>(BR)EBO</sub>	5	_	_	V
at - $I_E$ = 10 $\mu$ A	V (BR)EBU	•			V
Collector Emitter Saturation Voltage	-V <sub>CE(sat)</sub>	_	_	35	mV
at $-I_C = 5 \text{ mA}$ , $-I_B = 0.5 \text{ mA}$	V CE(sat)			00	111.0
Collector Emitter Saturation Voltage	-V <sub>CE(sat)</sub>	_	_	120	mV
at $-I_C = 100 \text{ mA}$ , $-I_B = 10 \text{ mA}$	V CE(sat)			120	111 V
Transition Frequency	f⊤	_	250	_	MHz
at $-V_{CE} = 10 \text{ V}$ , $-I_{C} = 50 \text{ mA}$	' '		230	_	1711 12
Output Capacitance	C <sub>ob</sub>	_	13	_	pF
at $-V_{CB} = 10 \text{ V}$ , f = 1 MHz	Oob		13		Pi

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#### **Rating And Characteristic Curves**



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